

#19

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Takashi IPPOSHI, et al.

SERIAL NO: 09/930,202

GAU: 2815

RCE FILED: Herewith

EXAMINER: NGUYEN, JOSEPH H.

FOR: SEMICONDUCTOR WAFER

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

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SIR:

Applicant(s) wish to disclose the following information.

MAR 22 2004

REFERENCES

OFFICE OF PETITIONS

- ☒ The applicant(s) wish to make of record the references listed on the attached French Preliminary Search Report and on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION


- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 212812US2		SERIAL NO. 09/930,202	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Takashi IPPOSHI, et al.			
				FILING DATE RCE Filed Herewith		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AG						
	AD						
	AE						
	AF						
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	AH						
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	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	JP05090117	04/09/93	JAPAN W/ENGLISH ABSTRACT			X
	AP	JP01241854	09/26/89	JAPAN W/ENGLISH ABSTRACT			X
	AQ	JP56060061	05/23/81	JAPAN W/ENGLISH ABSTRACT			X
	AR	JP06005569	01/14/94	JAPAN W/ENGLISH ABSTRACT			X
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Effect of <100> Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15µm Gate Length, H. Sayama, et al.; International Electron Devices Meeting 1999; IEDM. Technical Digest, Washington, DC; Dec. 5-8, 1999; New York, NY; IEEE US; pp. 657-660.					
	AX	Smart Cut: A Promising New SOI Material Technology; Bruel, M. et al.; 1995 IEEE International SOI Conference Proceedings; Tuscon, Oct. 3-5, 1995; Proceedings of the Annual SOS/SOI Technology Conference. (From 1991 Proceedings of the International SOI Conference.) Silicon-on-Insulator Technology and Devices, New York, Oct. 3, 1995; pp. 178-179.					
	AY	High-Quality Epitaxial Layer Transfer (Eltran) by Bond and Etch-Back of Porous Si; Sato, et al.; 1995 IEEE International SOI Conference Proceedings. Tuscon, Oct. 3-5, 1995; Proceedings of the Annual SOS/SOI Technology Conference. (From 1991 Proceedings of the International SOI Conference.) Silicon-On-Insulator Technology and Devices, New York, Oct. 3, 1995, pp. 176-177.					
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							